

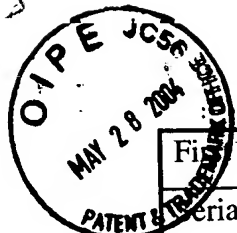
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First Named Inventor	Kirk D. Prall	GENERAL TRANSMITTAL FORM UNDER 37 CFR 1.8 (LARGE ENTITY)
Serial No.	10/738,408	
Filing Date	December 16, 2003	
Group Art Unit	2818	
Examiner Name	Unknown	
Confirmation No.	8316	
Attorney Docket No.	400.249US01	
Title: NROM MEMORY CELL, MEMORY ARRAY, RELATED DEVICES AND METHODS		

Mail Stop Amendment
Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

Enclosures					
The following documents are enclosed:					
<input checked="" type="checkbox"/>	Information Disclosure Statement (1 pg.); Form 1449 (7 pgs.); 66 copies of cited references; U.S. reference(s) not included pursuant to 37 C.F.R. 1.98 (c)(2)(i);				
<input checked="" type="checkbox"/>	An itemized return-receipt postcard				
Leffert Jay & Polglaze, P.A. P.O. Box 581009 Minneapolis, MN 55458-1009 T - 612/312-2200 F - 612/312-2250					
Please charge any additional fees or credit any overpayments to Deposit Account No. 501373.					
CUSTOMER NO. 27073					
Submitted By					
Name	Kenneth W. Bolvin	Reg. No.	34,125	Telephone	(612) 312-2211
Signature				Date	5/26/04
Certificate of Mailing					
I certify that this correspondence and the identified documents listed on this transmittal are being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Mail Stop Amendment, Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-1450 on May 26, 2004.					
Name	Rhonda L. Foley	Signature			

(LARGE ENTITY TRANSMITTAL UNDER 37 CFR § 1.8)



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In compliance with 37 C.F.R. §§ 1.56 and 1.97, *et seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified Application. Pursuant to 37 C.F.R. 1.98 (a)(2)(i), as this application was filed after June 30, 2003, Applicant has not included copies of U.S. Patents or U.S. Patent Applications. Applicant respectfully requests that this Information Disclosure Statement be entered and the references listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to MPEP §609, Applicant further requests that the Examiner initial next to each reference on the Form 1449 to indicate that the listed references have been considered. Applicant further requests that a copy of the initialed Form 1449 be returned with the next official communication.

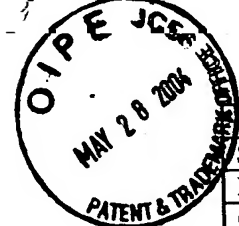
As an Office Action has not yet issued in this application, Applicant believes that no fees are due. However, the Commissioner for Patents is hereby authorized to charge any additional fees to Deposit Account No. 501373. If the Examiner has any questions or concerns regarding this application, please contact the undersigned at (612) 312-2211.

Date: 5/26/04

Respectfully submitted,
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Examiner Signature		Date Considered	
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